Konstantin Z Rushchanskii

List of Publications by Year
in descending order

15	423	840776 11	996975 15
papers	citations	h-index	g-index

15	15	15	684
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Ordering of Oxygen Vacancies and Related Ferroelectric Properties in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>HfO</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn><mml:mn> Physical Review Letters, 2021, 127, 087602.	7.8	31
2	Unconventional Ferroelectric Switching via Local Domain Wall Motion in Multiferroic Îµâ€²Fe₂O₃ Films. Advanced Electronic Materials, 2020, 6, 1901134.	5.1	11
3	Ab initiophase diagrams of Hfâ€“O, Zrâ€“O and Yâ€“O: a comparative study. Faraday Discussions, 2019, 213, 321-337.	3.2	27
4	Phase-change memories (PCM) â€“ Experiments and modelling: general discussion. Faraday Discussions, 2019, 213, 393-420.	3.2	7
5	Routes for increasing endurance and retention in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>HfO</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math> -based resistive switching memories. Physical Review Materials, 2018, 2, .	2.4	18
6	Melting of Pb Charge Glass and Simultaneous Pbâ€“Cr Charge Transfer in PbCrO₃ as the Origin of Volume Collapse. Journal of the American Chemical Society, 2015, 137, 12719-12728.	13.7	45
7	First-principles prediction of oxygen octahedral rotations in perovskite-structure EuTiO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review B, 2012, 85, .	3.2	55
8	Ab InitioPhonon Structure ofh-YMnO₃in Low-Symmetry Ferroelectric Phase. Ferroelectrics, 2012, 426, 90-96.	0.6	4
9	Vacancy-mediated diffusion in biaxially strained Si. Applied Physics Letters, 2011, 98, 031908.	3.3	11
10	A multiferroic material to search for the permanent electric dipole moment of the electron. Nature Materials, 2010, 9, 649-654.	27.5	88
11	Stress enhanced self-diffusion in Si: Entropy effect in anisotropic elastic environment. Applied Physics Letters, 2008, 92, 152110.	3.3	6
12	Ferroelectricity, Nonlinear Dynamics, and Relaxation Effects in Monoclinic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Sn</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">P</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:mn>6</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2007, 99, 207601.	7.8	54
13	Influence of pressure on the structural, dynamical, and electronic properties of theSnP2S6layered crystal. Physical Review B, 2006, 73, .	3.2	23
14	Similarities of the band structure of In4Se3 and InSe under pressure and peculiarities of the creation of the band gap. Physica Status Solidi (B): Basic Research, 2006, 243, 592-609.	1.5	35
15	Band structure calculations on the layered compounds FeGa 2 S 4 and NiGa 2 S 4. Journal of Physics and Chemistry of Solids, 2002, 63, 2019-2028.	4.0	13